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Team Nexperia

# 74HC7540; 74HCT7540

Octal Schmitt trigger buffer/line driver; 3-state; inverting

Rev. 5 — 26 May 2016

Product data

Product data sheet

#### 1. **General description**

The 74HC7540; 74HCT7540 is an 8-bit inverting buffer/line driver with Schmitt-trigger inputs and 3-state outputs. The device features two output enables (OE1 and OE2). A HIGH on OEn causes the outputs to assume a high-impedance OFF-state. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V<sub>CC</sub>. Schmitt trigger inputs transform slowly changing input signals into sharply defined jitter-free output signals.

#### 2. **Features and benefits**

- Input levels:
  - ◆ For 74HC7540: CMOS level
  - ◆ For 74HCT7540: TTL level
- Inverting outputs
- Low-power dissipation
- Complies with JEDEC standard no. 7 A
- Multiple package options
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

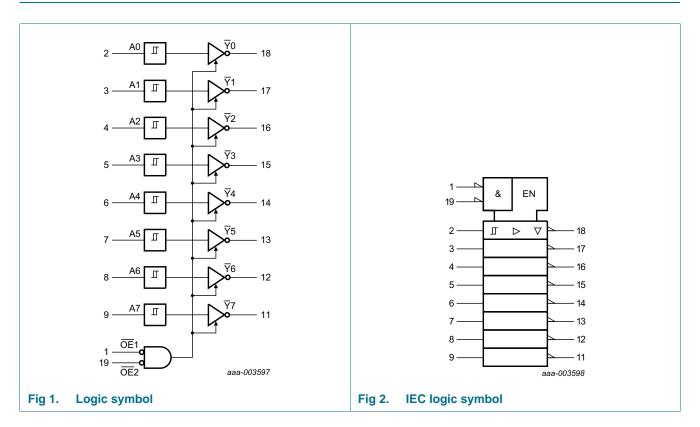
#### Ordering information 3.

Table 1. **Ordering information** 

Type number	Package									
	Temperature range	Name	Description	Version						
74HC7540D	−40 °C to +125 °C	SO20	plastic small outline package; 20 leads;	SOT163-1						
74HCT7540D			body width 7.5 mm							
74HC7540DB	–40 °C to +125 °C	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1						

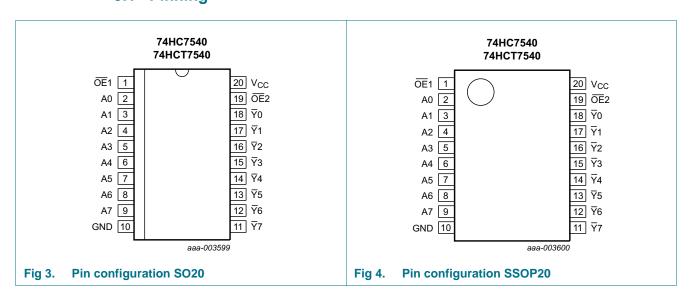


## 4. Functional diagram



## 5. Pinning information

## 5.1 Pinning



## 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
OE1	1	output enable input (active LOW)
A0 to A7	2, 3, 4, 5, 6, 7, 8, 9	data input
GND	10	ground (0 V)
$\overline{Y}$ 0 to $\overline{Y}$ 7	18, 17, 16, 15, 14, 13, 12, 11	data output
OE2	19	output enable input (active LOW)
V <sub>CC</sub>	20	supply voltage

## 6. Functional description

Table 3. Functional table[1]

		Input	Output
OE1	OE2	An	Yn
L	L	L	Н
L	L	Н	L
Χ	Н	X	Z
Н	X	X	Z

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC</sub>	supply voltage			-0.5	+7	V
I <sub>IK</sub>	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$	<u>[1]</u>	-	±20	mA
I <sub>OK</sub>	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u>	-	±20	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$		-	±35	mA
I <sub>CC</sub>	supply current			-	70	mA
I <sub>GND</sub>	ground current			-70	-	mA
T <sub>stg</sub>	storage temperature			-65	+150	°C
P <sub>tot</sub>	total power dissipation	SO20, SSOP20	[2]	-	500	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>[2]</sup> For SO20 package: above 70 °C the value of  $P_{tot}$  derates linearly with 8 mW/K. For SSOP20 package: above 60 °C the value of  $P_{tot}$  derates linearly with 5.5 mW/K.

# 8. Recommended operating conditions

## Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	7	74HC7540			74HCT7540			
			Min	Тур	Max	Min	Тур	Max		
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V	
VI	input voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V	
Vo	output voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V	
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C	

## 9. Static characteristics

### Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Tar	<sub>nb</sub> = 25	°C	T <sub>amb</sub> = -40 °C to +85 °C		T <sub>amb</sub> = -40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC754	40									
V <sub>OH</sub>	HIGH-level	$V_I = V_{T+}$ or $V_{T-}$								
	output voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V <sub>OL</sub>	LOW-level	$V_I = V_{T+}$ or $V_{T-}$								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_O = 7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
l <sub>OZ</sub>	OFF-state output current	$V_I = V_{T+}$ or $V_{T-}$ ; $V_{CC} = 6.0 \text{ V}$ ; $V_O = V_{CC}$ or GND	-	-	±0.5	-	±5.0	-	±10	μА
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT7	540	1		1		1	1	1	1	
V <sub>OH</sub>	HIGH-level	$V_{I} = V_{T+} \text{ or } V_{T-}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -6.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T <sub>amb</sub> = 25 °C				= –40 °C 85 °C	T <sub>amb</sub> = -40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
V <sub>OL</sub>	LOW-level	$V_{I} = V_{T+} \text{ or } V_{T-}; V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = 20 \mu A;$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 6.0 \text{ mA};$	-	0.15	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I <sub>OZ</sub>	OFF-state output current	$V_I = V_{T+}$ or $V_{T-}$ ; $V_{CC} = 5.5$ V; $V_O = V_{CC}$ or GND	-	-	±0.5	-	±5.0	-	±10	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Δl <sub>CC</sub>	additional supply current	per input pin; $I_O = 0$ A; $V_I = V_{CC} - 2.1$ V; other inputs at $V_{CC}$ or GND; $V_{CC} = 4.5$ V to 5.5 V								
		An input	-	20	72	-	90	-	98	μΑ
		OEn input	-	130	468	-	585	-	637	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

# 10. Dynamic characteristics

#### Table 7. Dynamic characteristics

 $GND = 0 \ V; \ C_L = 50 \ pF;$  for test circuit see Figure 7.

Symbol	Parameter	Conditions	Т	<sub>amb</sub> = 2	5 ℃	$T_{amb} = -40^{\circ}$	°C to +125 °C	Unit
			Min	Тур	Max	Max (85 °C)	Max (125 °C)	
74HC754	40							
t <sub>pd</sub>	propagation delay	An to Yn; see Figure 5	[1]					
		V <sub>CC</sub> = 2.0 V	-	39	120	150	180	ns
		V <sub>CC</sub> = 4.5 V	-	14	24	30	36	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	11	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	11	20	26	31	ns
t <sub>en</sub>	enable time	OEn to Yn; see Figure 6	[1]					
		V <sub>CC</sub> = 2.0 V	-	41	150	190	225	ns
		V <sub>CC</sub> = 4.5 V	-	15	30	38	45	ns
		V <sub>CC</sub> = 6.0 V	-	12	26	33	38	ns
t <sub>dis</sub>	disable time	OEn to Yn; see Figure 6	[1]					
		V <sub>CC</sub> = 2.0 V	-	52	150	190	225	ns
		V <sub>CC</sub> = 4.5 V	-	19	30	38	45	ns
		V <sub>CC</sub> = 6.0 V	-	15	26	33	38	ns

 Table 7.
 Dynamic characteristics

 $GND = 0 \ V; \ C_L = 50 \ pF;$  for test circuit see <u>Figure 7</u>.

Symbol	Parameter	Conditions		Tan	<sub>nb</sub> = 25	°C	T <sub>amb</sub> = -40 °	C to +125 °C	Unit
				Min	Тур	Max	Max (85 °C)	Max (125 °C)	
t <sub>t</sub>	transition time	see Figure 5	[2]						
		V <sub>CC</sub> = 2.0 V		-	14	60	75	90	ns
		V <sub>CC</sub> = 4.5 V		-	5	12	15	18	ns
		V <sub>CC</sub> = 6.0 V		-	4	10	13	15	ns
C <sub>PD</sub>	power dissipation capacitance	per package; V <sub>I</sub> = GND to V <sub>CC</sub>	[3]	-	29	-	-	-	pF
74HCT7	540							-1	
t <sub>pd</sub>	propagation delay	An to Yn; see Figure 5	[1]						
		V <sub>CC</sub> = 4.5 V		-	19	32	40	48	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	16	-	-	-	ns
t <sub>en</sub>	enable time	OEn to Yn; see Figure 6	[1]						
		V <sub>CC</sub> = 4.5 V		-	19	32	40	48	ns
t <sub>dis</sub>	disable time	OEn to Yn; see Figure 6	[1]						
		V <sub>CC</sub> = 4.5 V		-	20	32	40	48	ns
t <sub>t</sub>	transition time	V <sub>CC</sub> = 4.5 V; see <u>Figure 5</u>	[2]	-	5	12	15	18	ns
C <sub>PD</sub>	power dissipation capacitance	per package; V <sub>I</sub> = GND to V <sub>CC</sub> – 1.5 V	[3]	-	31	-	-	-	pF

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

 $t_{\text{en}}$  is the same as  $t_{\text{PZL}}$  and  $t_{\text{PZH}}.$ 

 $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ .

- [2]  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .
- [3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ):

$$P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \sum \left( C_L \times V_{CC}{}^2 \times f_o \right)$$
 where:

 $f_i$  = input frequency in MHz;

 $f_o$  = output frequency in MHz;

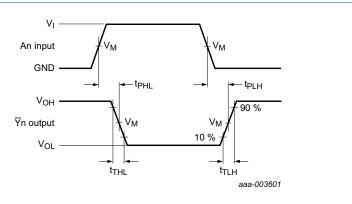
C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_0) = \text{sum of outputs.}$ 

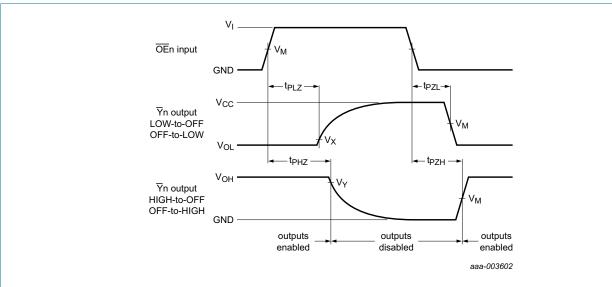
## 11. Waveforms



Measurement points are given in Table 8.

 $V_{\text{OL}}$  and  $V_{\text{OH}}$  are typical voltage output levels that occur with the output load.

Fig 5. Input to output propagation delays



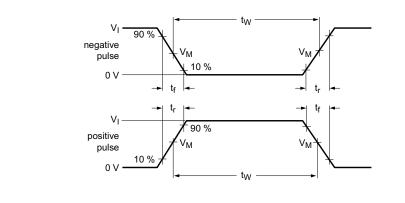
Measurement points are given in Table 8.

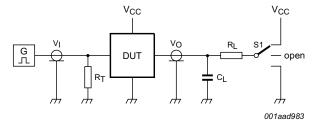
 $V_{\mbox{\scriptsize OL}}$  and  $V_{\mbox{\scriptsize OH}}$  are typical voltage output levels that occur with the output load.

Fig 6. 3-state enable and disable times

Table 8. Measurement points

Туре	Input	Output		
	$V_{M}$	V <sub>M</sub>	$V_X$	V <sub>Y</sub>
74HC7540	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>	0.1V <sub>CC</sub>	0.9V <sub>CC</sub>
74HCT7540	1.3 V	1.3 V	0.1V <sub>CC</sub>	0.9V <sub>CC</sub>





Test data is given in Table 9.

Definitions test circuit:

 $R_T$  = Termination resistance should be equal to output impedance  $Z_0$  of the pulse generator

C<sub>L</sub> = Load capacitance including jig and probe capacitance

R<sub>L</sub> = Load resistance

S1 = Test selection switch

Fig 7. Test circuit for measuring switching times

Table 9. Test data

Туре	Input		Load		S1 position			
	VI	t <sub>r</sub> , t <sub>f</sub>	CL	R <sub>L</sub>	t <sub>PHL</sub> , t <sub>PLH</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>	
74HC7540	V <sub>CC</sub>	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V <sub>CC</sub>	
74HCT7540	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V <sub>CC</sub>	

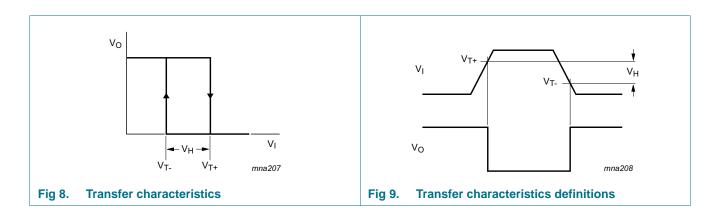
## 12. Transfer characteristics

Table 10. Transfer characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); see Figure 8 and Figure 9.

Symbol	Parameter	Conditions	T <sub>ar</sub>	<sub>nb</sub> = 25	°C	T <sub>amb</sub> = -40 °C to +85 °C		T <sub>amb</sub> = -40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC754	40									
V <sub>T+</sub>	positive-going	V <sub>CC</sub> = 2.0 V	-	-	1.5	-	1.5	-	1.5	V
	threshold	V <sub>CC</sub> = 4.5 V	-	-	3.15	-	3.15	-	3.15	V
	voltage	V <sub>CC</sub> = 6.0 V	-	-	4.2	-	4.2	-	4.2	V
$V_{T-}$	negative-going	V <sub>CC</sub> = 2.0 V	0.3	-	-	0.3	-	0.3	-	V
	threshold voltage	V <sub>CC</sub> = 4.5 V	1.35	-	-	1.35	-	1.35	-	V
		V <sub>CC</sub> = 6.0 V	1.8	-	-	1.8	-	1.8	-	V
V <sub>H</sub>	hysteresis	V <sub>CC</sub> = 2.0 V	0.1	0.20	-	0.1	-	0.1	-	V
	voltage	V <sub>CC</sub> = 4.5 V	0.25	0.40	-	0.25	-	0.25	-	V
		V <sub>CC</sub> = 6.0 V	0.3	0.5	-	0.3	-	0.3	-	V
74HCT7	540									
V <sub>T+</sub>	positive-going	V <sub>CC</sub> = 4.5 V	-	-	2.0	-	2.0	-	2.0	V
	threshold voltage	V <sub>CC</sub> = 5.5 V	-	-	2.1	-	2.1	-	2.1	V
$V_{T-}$	negative-going	V <sub>CC</sub> = 4.5 V	0.7	-	-	0.64	-	0.6	-	V
	41 1 - 1 - 1	V <sub>CC</sub> = 5.5 V	0.8	-	-	0.74	-	0.7	-	V
V <sub>H</sub>	hysteresis	V <sub>CC</sub> = 4.5 V	0.17	0.23	-	-	-	-	-	V
	voltogo	V <sub>CC</sub> = 5.5 V	0.17	0.23	-	-	-	-	-	V

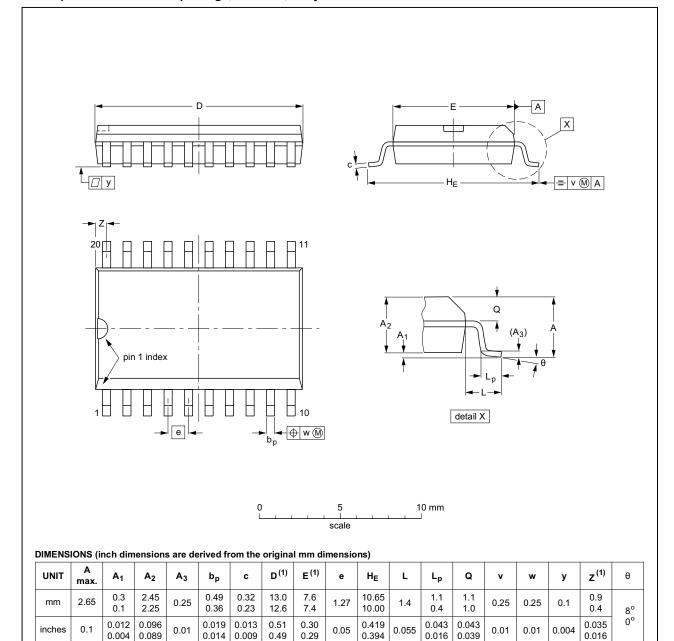
## 13. Transfer characteristics waveforms



## 14. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1



#### Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	
SOT163-1	075E04	MS-013				<del>-99-12-27</del> 03-02-19

Fig 10. Package outline SOT163-1 (SO20)

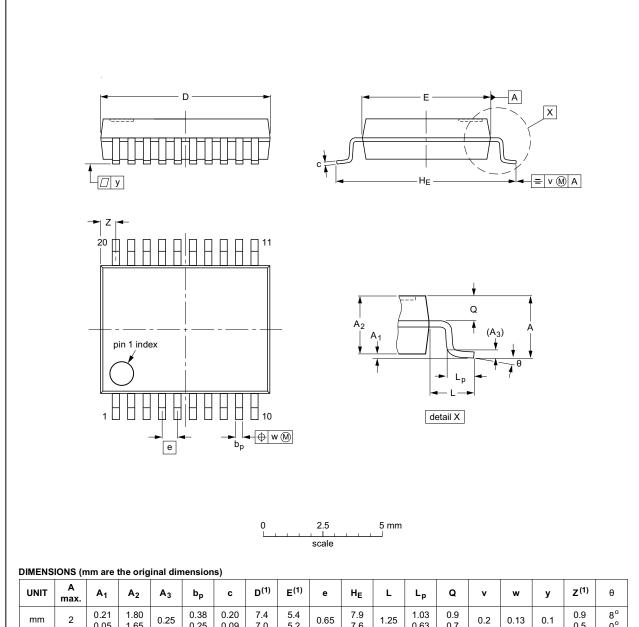
74HC\_HCT7540

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SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm

SOT339-1



						-,												
UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	7.4 7.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	0.9 0.5	8° 0°

1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT339-1		MO-150				<del>99-12-27</del> 03-02-19

Fig 11. Package outline SOT339-1 (SSOP20)

74HC\_HCT7540

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## 15. Abbreviations

#### Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

# 16. Revision history

#### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
74HC_HCT7540 v.5	20160526	Product data sheet	-	74HC_HCT7540 v.4		
Modifications:	Type numbers	s 74HC7540N and 74HCT7540	ON (SOT146-1) remo	oved.		
	• <u>Table 6</u> : cond	itions for OFF-state output cur	rent have changed.			
74HC_HCT7540 v.4	20121231	Product data sheet	-	74HC_HCT7540 v.3		
Modifications:	<ul> <li>I<sub>OZ</sub> added to s</li> </ul>	static characteristics table.				
74HC_HCT7540 v.3	20120827	Product data sheet	-	74HC_HCT7540_CNV v.2		
Modifications:		this data sheet has been rede NXP Semiconductors.	signed to comply wi	th the new identity		
	<ul> <li>Legal texts ha</li> </ul>	ave been adapted to the new c	ompany name wher	e appropriate.		
74HC_HCT7540_CNV v.2	19970917	Product specification	-	-		

## 17. Legal information

#### 17.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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# 74HC7540; 74HCT7540

## Octal Schmitt trigger buffer/line driver; 3-state; inverting

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